L Number	Hits	Search Text	DB	Time stamp
-	0	(depolarization or (charge adj reduct?\$5) or (electrostatic adj discharge) or (electrostatic adj depolarization)) same (plasma adj flood adj gun)	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2003/03/27 11:55
_	237	(depolarization or (charge adj reduct?\$5) or (electrostatic adj discharge) or (electrostatic adj depolarization)) same plasma	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2003/03/27 10:20
-	4068	((depolarization or (charge adj reduct?\$5) or (electrostatic adj discharge) or (electrostatic adj depolarization)) same plasma) (wafer adj	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2003/03/27
-	30	fabrication)	IBM_TDB, USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/27 10:25
-	79	depolarization adj (method or process)	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2003/03/27 10:25
_	90	((charge adj reduct?\$5) or depolarization) adj (method or process)	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2003/03/27 10:26
-	0	(((charge adj reduct?\$5) or depolarization) adj (method or process)) and (expos?\$5 with plasma)	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2003/03/27 10:27
-	11	(((charge adj reduct?\$5) or depolarization) adj (method or process)) and plasma	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2003/03/27 10:27
-	7553	(depolarization or (de adj polarization))	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2003/03/27 12:03
_	6	((depolarization or (de adj polarization))) and (wafer adj fabricat?\$5)	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2003/03/27
-	12	((electrostatic adj discharge) or esd) with (wafer adj fabricat?\$5)	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2003/03/27 12:02
-	0	(polarization adj charge?) with (wafer adj fabricat?\$5)	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2003/03/27 12:03
-	1	(depolarization or (de adj polarization)) with (wafer adj fabricat?\$5)	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2003/03/27 12:05
-	0	depolarization with (wafer near2 pad)	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2003/03/27 12:08
			IBM_TDB	

_	37	semiconductor adj fabrication adj tool?	USPAT; US-PGPUB;	2003/03/27 12:08
			EPO; JPO; DERWENT; IBM TDB	
 -	0	(semiconductor adj fabrication adj tool?)	USPĀT;	2003/03/27
		with (discharge near2 electrostatic)	US-PGPUB; EPO; JPO;	12:10
			DERWENT; IBM TDB	
_	0	(semiconductor adj fabrication adj tool?)	USPĀT;	2003/03/27
		<pre>with ((discharge near2 electrostatic) or esd or (electrostatic adj discharge))</pre>	US-PGPUB; EPO; JPO;	12:10
		esa or (erectionedere aaj arsonarge,)	DERWENT;	
_	0	(semiconductor adj fabrication adj tool?)	IBM_TDB USPAT;	2003/03/27
		same ((discharge near2 electrostatic) or	US-PGPUB;	12:11
		esd or (electrostatic adj discharge))	EPO; JPO; DERWENT;	
			IBM_TDB	2002/02/27
-	207	(ion adj implantation) same ((electrostatic adj charge) or esd or	USPAT; US-PGPUB;	2003/03/27
		(electrostatic adj discharge))	EPO; JPO;	
			DERWENT; IBM TDB	
-	41	((ion adj implantation) same	USPĀT;	2003/03/27
		((electrostatic adj charge) or esd or (electrostatic adj discharge))) and	US-PGPUB; EPO; JPO;	12:12
		plasma	DERWENT; IBM TDB	
_	1	(wafer near2 pad) with (depolarization or	USPAT;	2003/03/27
		(de adj polarization) or (electrostatic adj discharge) or esd or (charge near2	US-PGPUB; EPO; JPO;	12:45
		(reduct?\$5 or neutralization)))	DERWENT;	
	4	(("5089710") or ("5399871")).PN.	IBM_TDB USPAT;	2003/03/27
]	((3003/10 / 31 (33338/1 ///	US-PGPUB;	13:25
			EPO; JPO; DERWENT;	
			IBM_TDB USPAT;	2003/03/27
_	0	("(insulating near2 pad) with plasma").PN.	US-PGPUB;	14:36
			EPO; JPO; DERWENT;	
			IBM TDB	
_	14	(insulating near2 pad) with plasma	USPAT; US-PGPUB;	2003/03/27 14:38
			EPO; JPO;	
			DERWENT; IBM_TDB	
-	118741	(H01L021/3065 or H01L021/205 or	USPAT; US-PGPUB;	2003/03/27
		H01L021/31 or H01L021/68).ipc.	EPO; JPO;	11.00
			DERWENT; IBM TDB	
-	23297		USPĀT;	2003/03/27
	-	H01L021/31 or H01L021/68).ipc.) and plasma	US-PGPUB; EPO; JPO;	14:39
		F = 2.100	DERWENT;	
_	3		IBM_TDB USPAT;	2003/03/27.
		H01L021/31 or H01L021/68).ipc.) and plasma) and (insulating near3 pad?)	US-PGPUB; EPO; JPO;	14:39
			DERWENT;	
	1381	depolarization and plasma	IBM_TDB USPAT;	2003/10/19
	1301	acporatization and prasma	US-PGPUB;	09:18
			EPO; JPO; DERWENT;	
			IBM TDB	

Depart D					1 / /
Comparization nearlo (fabrication with plasma) Comparization with plasma) Comparization with plasma Compar	-	3	depolarization and (exposing near5	USPAT;	2003/10/19
DEPMENT: IBM TDB USPAT: US-PGPUB; EPO; JPO; DEPMENT: IBM TDB USPAT:		1	plasma)		09.19
Component Comp					
Design D]				
Description	_	0	depolarization near10 (fabrication with	USPĀT;	2003/10/19
DERWENT; IBM TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT;	1				09:20
S depolarization and (fabrication with plasma) SPAT; 2003/10/19 09:22 09:23 09:27 09:28 09:2					
Separation and (fabrication with plasma)					
Description		_			2002/10/10
The content of the	-	5			1
181			plasma)		09.22
181 (depolariz\$5 or neutraliz\$5) and (fabrication with plasma) USPĀT;					
181 (depolariz\$5 or neutraliz\$5) and (fabrication with plasma)					
(fabrication with plasma)	_	181	(depolariz\$5 or neutraliz\$5) and		2003/10/19
Section Comparity Compar				US-PGPUB;	09:27
Section Sect		ï			
59258 (depolariz\$5 or neutraliz\$5 or reduc\$5) USPĀT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPĀT; USPĀT					
near5 (charge or electrostatic)					2002/10/10
Composition of the composition	_	59258	(depolariz\$5 or neutraliz\$5 or reduc\$5)	i	
Composition			nears (charge or electrostatic)	1	09.20
Composition of the composition				L .	
((depolariz\$5 or neutraliz\$5 or reduc\$5) near5 (charge or electrostatic)) and plasma ((depolariz\$5 or neutraliz\$5 or reduc\$5) near5 (charge or electrostatic)) near10 plasma ((depolariz\$5 or neutraliz\$5 or reduc\$5) plasma ((depolariz\$5 or neutraliz\$5 or reduc\$5) near5 (charge or electrostatic)) near10 plasma ((depolariz\$5 or neutraliz\$5 or reduc\$5) near5 (charge or electrostatic)) near5 (fabrication near5 plasma) ((depolariz\$5 or neutraliz\$5 or reduc\$5) near5 (charge or electrostatic)) near5 plasma (((depolariz\$5 or neutraliz\$5 or reduc\$5) near5 (charge or electrostatic)) near5 plasma (((depolariz\$5 or neutraliz\$5 or reduc\$5) near5 (charge or electrostatic)) near5 plasma (((depolariz\$5 or neutraliz\$5 or reduc\$5) near5 (charge or electrostatic)) near5 plasma) and wafer (((depolariz\$5 or neutraliz\$5 or reduc\$5) near5 (charge or electrostatic)) near5 plasma) and wafer (((depolariz\$5 or neutraliz\$5 or reduc\$5) near5 (charge or electrostatic)) near5 plasma) and wafer (((depolariz\$5 or neutraliz\$5 or reduc\$5) near5 (charge or electrostatic)) near5 plasma) ((((depolariz\$5 or neutraliz\$5 or reduc\$5) near5 (charge or electrostatic)) near5 plasma) ((((depolariz\$5 or neutraliz\$5 or reduc\$5) near5 (charge or electrostatic)) near5 plasma) ((((depolariz\$5 or neutraliz\$5 or reduc\$5) near5 (charge or electrostatic)) near5 plasma) ((((depolariz\$5 or neutraliz\$5 or reduc\$5) near5 (charge or electrostatic)) near5 plo; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; IBM_TDB USPAT; IBM_TDB USPAT; IBM_TDB USPAT;	1			,	
near5 (charge or electrostatic)) and plasma 19	_	6779	((depolariz\$5 or neutraliz\$5 or reduc\$5)		2003/10/19
Plasma		· · · · · ·	near5 (charge or electrostatic)) and		09:28
- 758 ((depolariz\$5 or neutraliz\$5 or reduc\$5) near5 (charge or electrostatic)) near10 plasma 2 ((depolariz\$5 or neutraliz\$5 or reduc\$5) near5 (charge or electrostatic)) near5 (fabrication near5 plasma) 4 ((depolariz\$5 or neutraliz\$5 or reduc\$5) near5 (charge or electrostatic)) near5 (plasma) 4 ((depolariz\$5 or neutraliz\$5 or reduc\$5) near5 (charge or electrostatic)) near5 plasma 5 ((depolariz\$5 or neutraliz\$5 or reduc\$5) near5 (charge or electrostatic)) near5 plasma 6 ((depolariz\$5 or neutraliz\$5 or reduc\$5) near5 (charge or electrostatic)) near5 plasma 6 ((depolariz\$5 or neutraliz\$5 or reduc\$5) near5 (charge or electrostatic)) near5 plasma) and wafer 6 ((depolariz\$5 or neutraliz\$5 or reduc\$5) near5 (charge or electrostatic)) near5 plasma) and wafer 6 ((depolariz\$5 or neutraliz\$5 or reduc\$5) near5 (charge or electrostatic)) near5 plasma) and wafer 6 ((depolariz\$5 or neutraliz\$5 or reduc\$5) near5 (charge or electrostatic)) near5 plasma) and wafer 6 ((depolariz\$5 or neutraliz\$5 or reduc\$5) near5 (charge or electrostatic)) near5 plasma) and wafer					
- 758 ((depolariz\$5 or neutraliz\$5 or reduc\$5) near5 (charge or electrostatic)) near10 plasma 2 ((depolariz\$5 or neutraliz\$5 or reduc\$5) near5 (charge or electrostatic)) near5 (fabrication near5 plasma) 4 ((depolariz\$5 or neutraliz\$5 or reduc\$5) near5 (charge or electrostatic)) near5 (fabrication near5 plasma) 4 ((depolariz\$5 or neutraliz\$5 or reduc\$5) near5 (charge or electrostatic)) near5 plasma 5 ((depolariz\$5 or neutraliz\$5 or reduc\$5) near5 (charge or electrostatic)) near5 plasma 6 ((depolariz\$5 or neutraliz\$5 or reduc\$5) near5 (charge or electrostatic)) near5 plasma) and wafer 6 (depolariz\$5 or neutraliz\$5 or reduc\$5) near5 (charge or electrostatic)) near5 plasma) and wafer 6 (depolariz\$5 or neutraliz\$5 or reduc\$5) near5 (charge or electrostatic)) near5 plasma) and wafer 6 (depolariz\$5 or neutraliz\$5 or reduc\$5) near5 (charge or electrostatic)) near5 plasma) and wafer 7 (depolariz\$5 or neutraliz\$5 or reduc\$5) near5 (charge or electrostatic)) near5 plasma) and wafer 8 (depolariz\$5 or neutraliz\$5 or reduc\$5) NSPAT;					
near5 (charge or electrostatic)) near10 plasma 2 ((depolariz\$5 or neutraliz\$5 or reduc\$5) near5 (charge or electrostatic)) near5 (fabrication near5 plasma) 4 ((depolariz\$5 or neutraliz\$5 or reduc\$5) near5 (charge or electrostatic)) near5 (fabrication near5 plasma) 4 ((depolariz\$5 or neutraliz\$5 or reduc\$5) near5 (charge or electrostatic)) near5 plasma 5 ((depolariz\$5 or neutraliz\$5 or reduc\$5) near5 (charge or electrostatic)) near5 plasma 6 ((depolariz\$5 or neutraliz\$5 or reduc\$5) near5 (charge or electrostatic)) near5 plasma) and wafer 6 (depolariz\$5 or neutraliz\$5 or reduc\$5) near5 (charge or electrostatic)) near5 plasma) and wafer 6 (depolariz\$5 or neutraliz\$5 or reduc\$5) near5 (charge or electrostatic)) near5 plasma) and wafer 6 (depolariz\$5 or neutraliz\$5 or reduc\$5) NEWENT; NEW TDB NEWENT;			21.05		2002/10/10
plasma 2 ((depolariz\$5 or neutraliz\$5 or reduc\$5) DERWENT; IBM_TDB	-	758	((depolariz\$5 or neutraliz\$5 or reduc\$5)		1
DERWENT; IBM_TDB USPĀT; US-PGPUB; (fabrication near5 plasma) 612 ((depolariz\$5 or neutraliz\$5 or reduc\$5) near5 (charge or electrostatic)) near5 (fabrication near5 plasma) 612 ((depolariz\$5 or neutraliz\$5 or reduc\$5) near5 (charge or electrostatic)) near5 plasma 612 (((depolariz\$5 or neutraliz\$5 or reduc\$5) near5 (charge or electrostatic)) near5 plasma 613 (((depolariz\$5 or neutraliz\$5 or reduc\$5) near5 (charge or electrostatic)) near5 plasma) and wafer 614 ((depolariz\$5 or neutraliz\$5 or reduc\$5) near5 (charge or electrostatic)) near5 plasma) and wafer 615 DERWENT; IBM_TDB USPĀT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPĀT;	i				03.20
2 ((depolariz\$5 or neutraliz\$5 or reduc\$5)			brazma		
- 2 ((depolariz\$5 or neutraliz\$5 or reduc\$5) near5 (charge or electrostatic)) near5 (fabrication near5 plasma) - 612 ((depolariz\$5 or neutraliz\$5 or reduc\$5) near5 (charge or electrostatic)) near5 plasma - 302 (((depolariz\$5 or neutraliz\$5 or reduc\$5) near5 (charge or electrostatic)) near5 plasma - 302 (((depolariz\$5 or neutraliz\$5 or reduc\$5) near5 (charge or electrostatic)) near5 plasma) and wafer - 36283 (depolariz\$5 or neutraliz\$5 or reduc\$5) USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT;	1				
near5 (charge or electrostatic)) near5 (fabrication near5 plasma) ((depolariz\$5 or neutraliz\$5 or reduc\$5)	_	2	((depolariz\$5 or neutraliz\$5 or reduc\$5)	USPĀT;	The state of the s
(fabrication near5 plasma) (fabrication near5 plasma) ((depolariz\$5 or neutraliz\$5 or reduc\$5)		-	near5 (charge or electrostatic)) near5		09:29
- 612 ((depolariz\$5 or neutraliz\$5 or reduc\$5)			(fabrication near5 plasma)		
- 612 ((depolariz\$5 or neutraliz\$5 or reduc\$5)				1	
near5 (charge or electrostatic)) near5 plasma (((depolariz\$5 or neutraliz\$5 or reduc\$5)) near5 (charge or electrostatic)) near5 near5 (charge or electrostatic)) near5 near5 (charge or electrostatic)) near5 plasma) and wafer (((depolariz\$5 or neutraliz\$5 or reduc\$5)) plasma) and wafer (depolariz\$5 or neutraliz\$5 or reduc\$5)	1	610	(/langlaniacs an montrolines or reduces)		2004/05/20:
plasma [EPO; JPO; DERWENT; IBM_TDB [USPAT; US-PGPUB; plasma] and wafer [EPO; JPO; DERWENT; IBM_TDB [US-PGPUB; EPO; JPO; DERWENT; IBM_TDB] [US-PGPUB; EPO; DERWENT;	-	612	nears (charge or electrostatic)) pears		
DERWENT; IBM_TDB USPAT; near5 (charge or electrostatic)) near5 plasma) and wafer [BM_TDB_USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; USPAT; USPAT;					
- 302 (((depolariz\$5 or neutraliz\$5 or reduc\$5) USPĀT; near5 (charge or electrostatic)) near5 US-PGPUB; plasma) and wafer EPO; JPO; DERWENT; IBM_TDB USPĀT; 2004/05/20	1		pa control		
near5 (charge or electrostatic)) near5	1				
plasma) and wafer plasma) and wafer EPO; JPO; DERWENT; IBM_TDB USPAT; 2004/05/20	-	302	(((depolariz\$5 or neutraliz\$5 or reduc\$5)		
DERWENT; IBM_TDB Jackson (depolariz\$5 or neutraliz\$5 or reduc\$5) USPAT; 2004/05/20			near5 (charge or electrostatic)) near5		13:15
IBM_TDB 36283 (depolariz\$5 or neutraliz\$5 or reduc\$5)			plasma) and water		
_ 36283 (depolariz\$5 or neutraliz\$5 or reduc\$5) USPAT; 2004/05/20				1	
1 JOZOJ (GCDOTALIZACO OL MEGGLATIBACO OL LOCALIZACIONI	1_	36283	(denolariz\$5 or neutraliz\$5 or reduc\$5)		2004/05/20
with plasma US-PGPUB; 13:53		30203			1
EPO; JPO;			F		
DERWENT;					
IBM_TDB					2004/05/20
- 5804 ((depolariz\$5 or neutraliz\$5 or reduc\$5) USPAT; 2004/05/20	-	5804		1	1
with plasma) and fabrication US-PGPUB; 13:18			with plasma) and fabrication		13.10
DERWENT;					
IBM TDB					
- 7713 ((depolariz\$5 or neutraliz\$5 or reduc\$5) USPAT; 2004/05/20	_	7713	((depolariz\$5 or neutraliz\$5 or reduc\$5)		2004/05/20
with plasma) and wafer US-PGPUB; 13:20				1	13:20
EPO; JPO;					,
DERWENT;				I .	
IBM_TDB JOHN ((depolarizes or neutralizes or reduces) USPAT; 2004/05/20			/// 1 2 2 5 5 5 5 5 5 65		2004/05/20
Joon ((depoiding of medical material)	-	3067			
with plasma) and electrostatic US-PGPUB; 13:28 EPO; JPO;			with brasma) and efectiostatic		13.20
DERWENT;					
IBM TDB					

_	436	((depolariz\$5 or neutraliz\$5 or reduc\$5)	USPAT;	2004/05/20
		with plasma) and misalignment	US-PGPUB;	13:34
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
-	77	plasma with (electrostatic adj charge?)	USPĀT;	2004/05/20
			US-PGPUB;	13:50
			EPO; JPO;	
			DERWENT;	
	1		IBM TDB	
-	2	5399871.pn.	USPĀT;	2004/05/20
		·	US-PGPUB;	13:50
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	74658	(depolariz\$5 or neutraliz\$5 or reduc\$5 or	USPAT;	2004/05/20
		discharg\$5) with plasma	US-PGPUB;	13:54
	:		EPO; JPO;	
			DERWENT;	
			IBM_TDB	
_	306		USPAT;	2004/05/20
		neutraliz\$5 or reduc\$5 or discharg\$5))	US-PGPUB;	13:55
		with plasma	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	2	ep-709877-\$.did.	USPAT;	2004/06/13
			US-PGPUB;	08:48
1			EPO; JPO;	1
			DERWENT;	
			IBM TDB	<u> </u>